

HIGH POWER AMPLIFIER DARLINGTON TRANSISTOR

KTD1630G is designed to suit for audio amplifier output stage. It has good quality sound with complementary Item.

FEATURES

- Complementary to KTB2630G
- High power Amplifier for 100W Audio
- High DC Current Gain $h_{FE} = 6,500 \sim 30,000$ ($V_{CE} = 4V, I_C = 7A$)
- Wide SOA

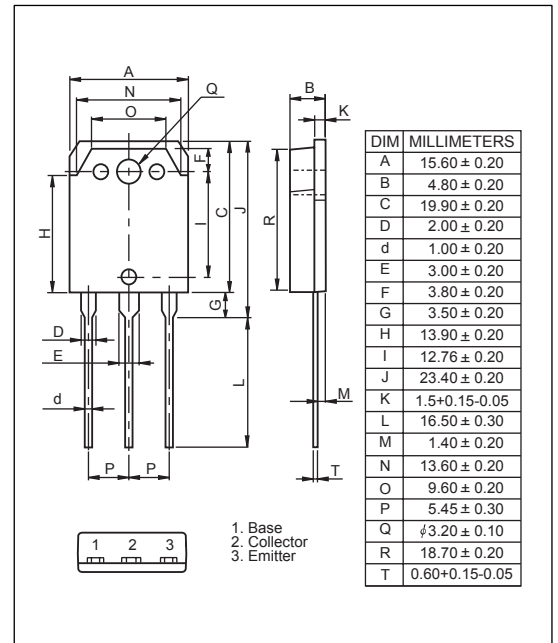
APPLICATIONS

- Audio amplifier output stage
- Series Regulator
- General Purpose

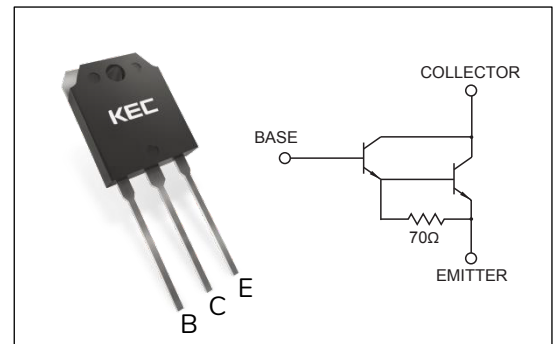
ORDERING INFORMATION

PART NUMBER	QTY per tube	Carton box
KTD1630G	30	1,800

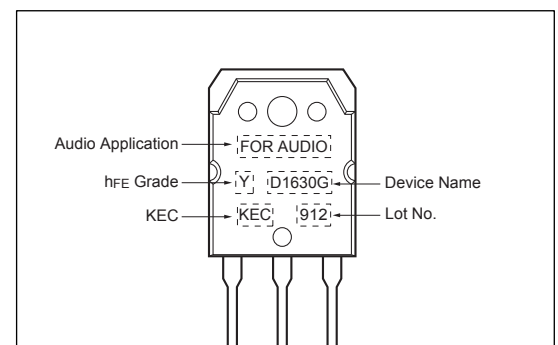
PACKAGE DIMENSION (TO-3P(N)-E)



PIN CONFIGURATION



MARKING CODE



PRODUCT DATASHEET

Darlington Transistor– KTD1630G

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	160	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	10	A
Base Current	I_B	1	A
Collector Power Dissipation ($T_C=25^\circ\text{C}$)	P_C	100	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C

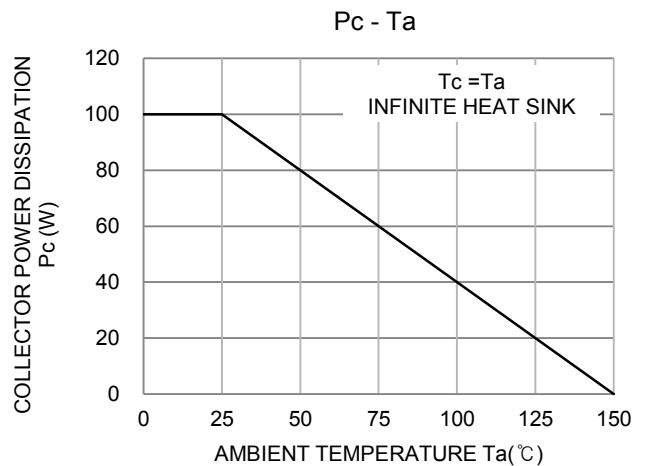
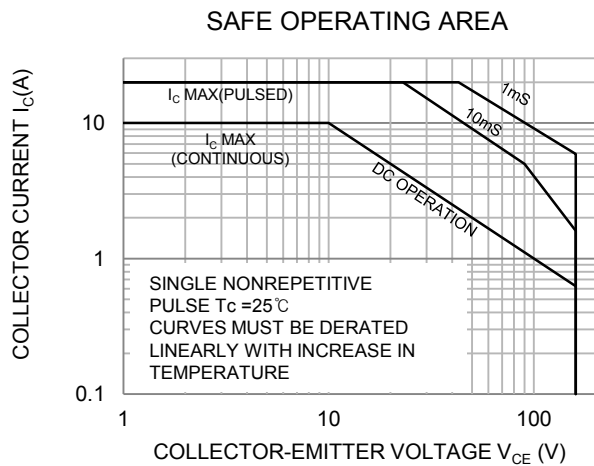
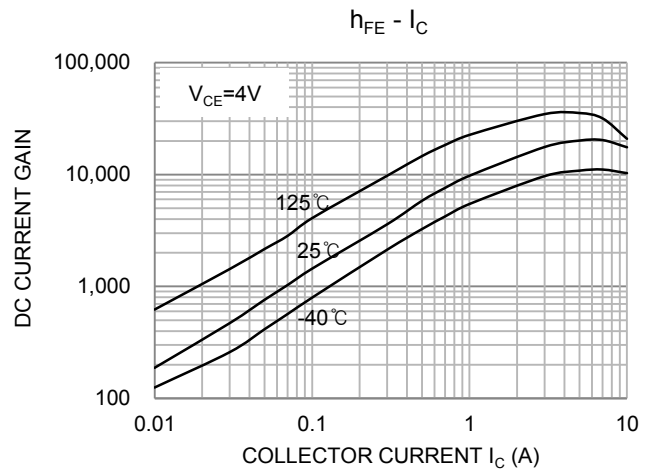
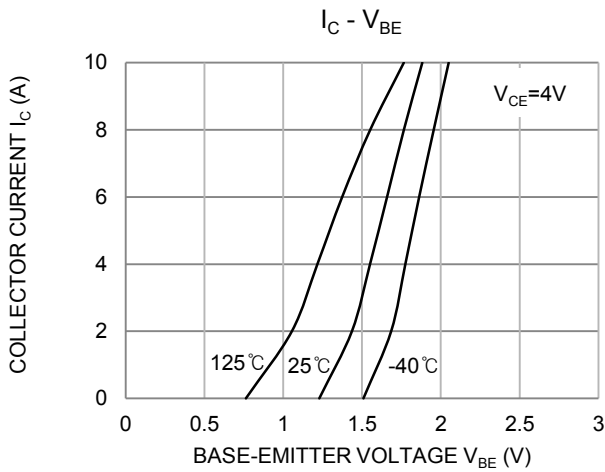
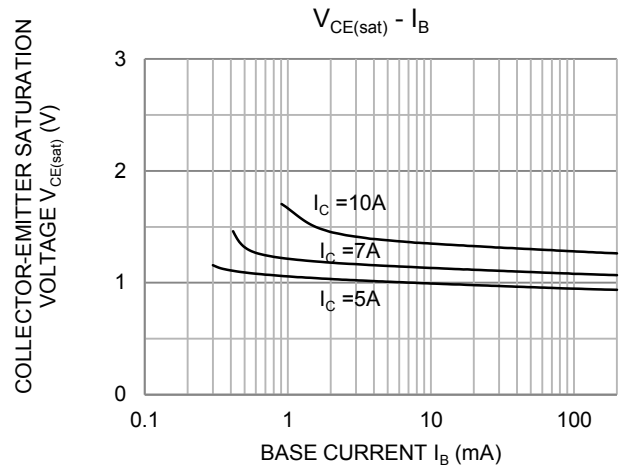
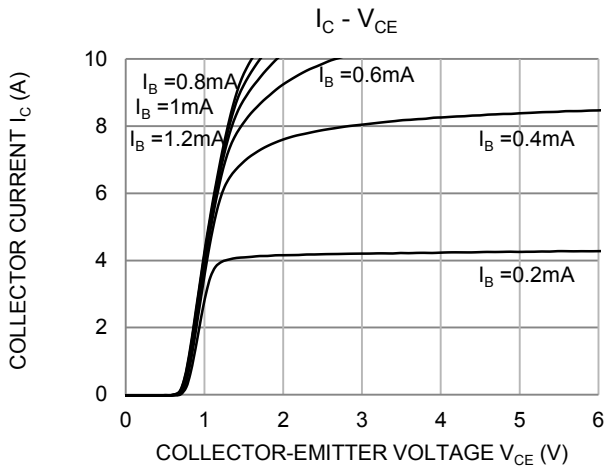
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=160\text{V}, I_E=0$	-	-	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$	-	-	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=30\text{mA}, I_B=0$	150	-	-	V
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=4\text{V}, I_C=7\text{A}$	6,500	-	30,000	-
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C=7\text{A}, I_B=7\text{mA}$	-	-	2.5	V
Base-Emitter Saturation Voltage	$V_{BE(\text{sat})}$	$I_C=7\text{A}, I_B=7\text{mA}$	-	-	3.0	V
Transition Frequency	f_T	$V_{CE}=12\text{V}, I_C=2\text{A}$	-	55	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}, I_E=0$	-	95	-	pF
Thermal Resistance	$R_{th(j-c)}$	Junction to case	-	-	1.25	°C/W

Note : h_{FE} Classification P: 6,500 ~ 20,000 Y : 15,000 ~ 30,000

PRODUCT DATASHEET

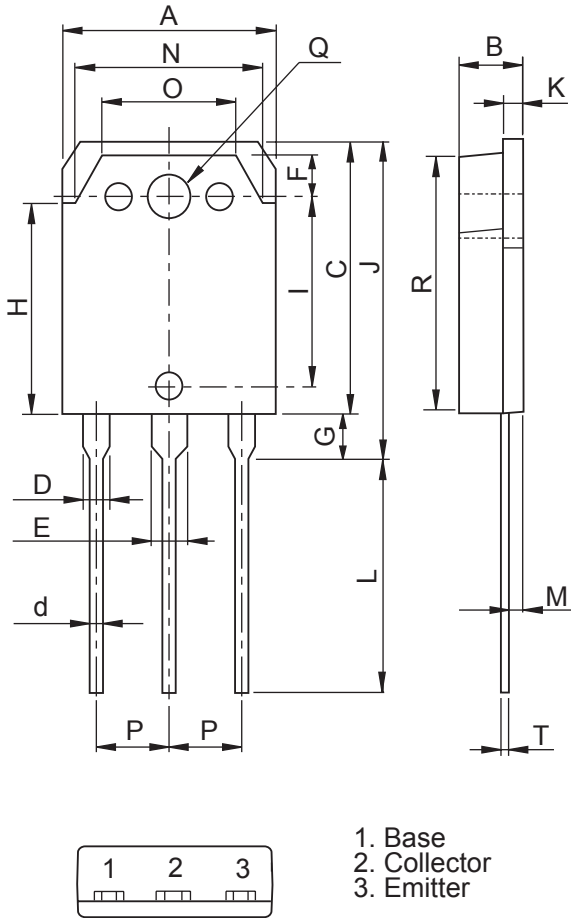
Darlington Transistor- KTD1630G



PRODUCT DATASHEET

Darlington Transistor- KTD1630G

PACKAGE INFORMATION (TO-3P(N)-E)



DIM	MILLIMETERS
A	15.60 ± 0.20
B	4.80 ± 0.20
C	19.90 ± 0.20
D	2.00 ± 0.20
d	1.00 ± 0.20
E	3.00 ± 0.20
F	3.80 ± 0.20
G	3.50 ± 0.20
H	13.90 ± 0.20
I	12.76 ± 0.20
J	23.40 ± 0.20
K	1.5+0.15-0.05
L	16.50 ± 0.30
M	1.40 ± 0.20
N	13.60 ± 0.20
O	9.60 ± 0.20
P	5.45 ± 0.30
Q	φ3.20 ± 0.10
R	18.70 ± 0.20
T	0.60+0.15-0.05

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1. The products described in this data are intended to be used in general-purpose electronic equipment (Office equipment, telecommunication equipment, measuring equipment, home appliances)
2. When you intend to use these products with equipment or device which require an extremely high of reliability and special applications (such as automobile, air travel aerospace, transportation equipment, life support, system and safety devices) in which special quality and reliability and the failure or malfunction of products may directly jeopardize or harm the human body or damage to property and any application other than the standard application intended, please be sure to consult with our sales representative in advance.
3. On designing your application, please use product within the ranges guaranteed by KEC for maximum rating, operating supply voltage range, heat radiation characteristics and other characteristics. User shall be responsible for failure or damage when used beyond the guaranteed ranges.
4. The technical information described in this data is limited to showing representative characteristics and applied circuit examples of the products and it does not constitute the warranting of industrial property, the granting of relative rights, or the granting of any license.
5. What are described in the data may be changed without any prior notice to reflect new technical development. Please confirm that you have received the latest product standards or specification before final design, purchase or use.
6. Although KEC is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors. Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. KEC shall have no responsibility for any damages arising out of the use of our Products beyond the rating specified by KEC.

For additional information,
please contact your local Sales Representative.

SOUTH KOREA (Headquarters)
KEC CORPORATION
PHONE : +82-2-2025-5000
sales@kec.co.kr

JAPAN
KEC JAPAN CO.,LTD.
PHONE : +81-03-5475-2691
kec_jp@kec.co.kr

SINGAPORE
KEC SINGAPORE PTE., LTD.
PHONE : +65-6748-7372(#102)
kec_twn@kec.co.kr

THAILAND
KEC THAILAND BANGKOK OFFICE
PHONE : +66-2-576-1484~5
kec_th@kec.co.kr

CHINA
KEC SHANGHAI CO.,LTD.
PHONE : +86-21-5490-2277
kec_sh@kec.co.kr

KEC SHENZHEN OFFICE
PHONE : +86-755-8882-9198
kec_hk@kec.co.kr

KEC TIANJIN OFFICE
PHONE : +86-22-2330-7562
kec_sh@kec.co.kr

HONG KONG
KEC HK CORP. LTD
PHONE : +852-2249-3734
kec_hk@kec.co.kr

TAIWAN
KEC TAIWAN CO.,LTD.
PHONE : +886-2-2515-8359
kec_twn@kec.co.kr

U.S.A
KEC AMERICA CORP.
PHONE : +1-714-259-0662
kec_a@kec.co.kr

